Rail-to-Rail Output, 3 MHz BW Operational Amplifier

The NCS2007 series operational amplifiers provide rail–to–rail output operation, 3 MHz bandwidth, and are available in single, dual, and quad configurations. Rail–to–rail operation enables the user to make optimal use of the entire supply voltage range while taking advantage of 3 MHz bandwidth. The NCS2007 can operate on supply voltages as low as 2.7 V over the temperature range of –40°C to 125°C . At a 2.7 V supply, the high bandwidth provides a slew rate of 2.1 V/µs while only consuming 405 µA of quiescent current per channel. The wide supply range allows the NCS2007 to run on supply voltages as high as 36 V, making it ideal for a broad range of applications. Since this is a CMOS device, high input impedance and low bias currents make it ideal for interfacing to a wide variety of signal sensors. The NCS2007 devices are available in a variety of compact packages.

Features

- Rail-To-Rail Output
- Wide Supply Range: 2.7 V to 36 V
- Wide Bandwidth: 3 MHz typical at $V_S = 2.7 \text{ V}$
- High Slew Rate: 2.8 V/ μ s typical at V_S = 2.7 V
- Low Supply Current: 405 μ A per channel at $V_S = 2.7 \text{ V}$
- Low Input Bias Current: 5 pA typical
- Wide Temperature Range: -40°C to 125°C
- Available in a variety of packages
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Current Sensing
- Signal Conditioning
- Automotive

End Products

- Notebook Computers
- Portable Instruments
- Power Supplies



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SOT-553 CASE 463B

TSOP-5 CASE 483





Micro8[™] CASE 846AH

SOIC-8 CASE 751





TSSOP-8 CASE 948S

UDFN8 CASE 517AC





TSSOP-14 CASE 948G

SOIC-14 NB CASE 751A

DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 2 of this data sheet.

ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.

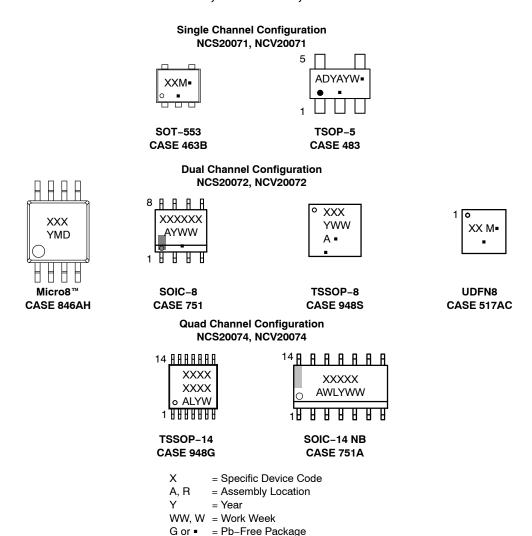
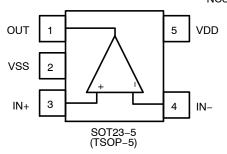
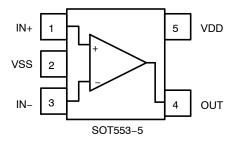


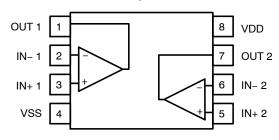
Figure 1. Marking Diagrams

Single Channel Configuration NCS20071, NCV20071





Dual Channel Configuration NCS20072, NCV20072



Quadruple Channel Configuration NCS20074, NCV20074

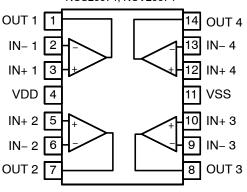


Figure 2. Pin Connections

ORDERING INFORMATION

Device	Configuration	Automotive	Marking	Package	Shipping [†]
NCS20071SN2T1G*		No	*	SOT23-5 (TSOP-5) (Pb-Free)	3000 / Tape and Reel
NCS20071*	0		*	SOT553-5 (Pb-Free)	4000 / Tape and Reel
NCV20071SN2T1G*	Single	Yes	*	SOT23-5 (TSOP-5) (Pb-Free)	3000 / Tape and Reel
NCV20071*	7		*	SOT553-5 (Pb-Free)	4000 / Tape and Reel
NCS20072DMR2G*			*	Micro8 (MSOP8) (Pb-Free)	4000 / Tape and Reel
NCS20072DR2G*			*	SOIC-8 (Pb-Free)	2500 / Tape and Reel
NCS20072DTBR2G*	1	No -	*	TSSOP-8 (Pb-Free)	3000 / Tape and Reel
NCS20072*	1		*	UDFN8 (Pb-Free)	3000 / Tape and Reel
NCV20072DMR2G*	Dual		*	Micro8 (MSOP8) (Pb-Free)	4000 / Tape and Reel
NCV20072DR2G*	7	V	*	SOIC-8 (Pb-Free)	2500 / Tape and Reel
NCV20072DTBR2G*	7	Yes	*	TSSOP-8 (Pb-Free)	3000 / Tape and Reel
NCV20072*	7		*	UDFN8 (Pb-Free)	3000 / Tape and Reel
NCS20074DR2G		NI-	NCS20074	SOIC-14 (Pb-Free)	3000 / Tape and Reel
NCS20074DTBR2G	0	No	NCS2 0074	TSSOP-14 (Pb-Free)	2500 / Tape and Reel
NCV20074DR2G	Quad	Van	NCS20074	SOIC-14 (Pb-Free)	3000 / Tape and Reel
NCV20074DTBR2G	7	Yes	NCS2 0074	TSSOP-14 (Pb-Free)	2500 / Tape and Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*Contact local sales office for more information

ABSOLUTE MAXIMUM RATINGS (Note 1)

	Rating		Symbol	Limit	Unit
Supply Voltage (V _{DD} – V _{SS}	s) (Note 2)		V _S	40	V
Input Voltage			V _I	V _{SS} – 0.2 to V _{DD} + 0.2	V
Differential Input Voltage		V _{ID} ±V _s			
Maximum Input Current			l _l	±10	mA
Maximum Output Current		I _O ±100			
Continuous Total Power Dis	ssipation (Note 2)		P_{D}	200	mW
Maximum Junction Temper	ature		TJ	150	°C
Storage Temperature Rang	ge		T _{STG}	-65 to 150	°C
Mounting Temperature (Infi	rared or Convection – 20 sec)		T _{mount}	260	°C
ESD Capability (Note 3)	Human Body Model Machine Model Charged Device Model		ESD _{HBM} ESD _{MM} ESD _{CDM}	2000 150 1000 (C6)	V
Latch-Up Current (Note 3)			I _{LU}	100	mA
Moisture Sensitivity Level (Note 3)		MSL	Level 1	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Refer to ELECTRICAL CHĂRACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.
- 2. Continuous short circuit operation to ground at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of the maximum output current rating over the long term may adversely affect reliability. Shorting output to either VDD or VSS will adversely affect reliability.

 3. This device series incorporates ESD protection and is tested by the following methods:
- - ESD Human Body Model tested per ANSI/ANSI/ESDA/JEDEC JS-001-2010 (AEC-Q100-002)
 - ESD Machine Model tested per JESD22–A115 (AEC-Q100-003)
 - ESD Charged Device Model tested per ANSI/ESD S5.3.1-2009 (AEC-Q100-011)
- 4. Latch-up Current tested per JEDEC standard: JESD78 (AEC-Q100-004) 5. Moisture Sensitivity Level tested per IPC/JEDEC standard: J-STD-020A

Parameter	Symbol	Package	Value	Unit
		SOT23-5/ TSOP5	235	
		SOT553-5	250	
		Micro8/MSOP8	238	
lunching to Ambient	0	SOIC-8	190	°C/W
Junction-to-Ambient	$\theta_{\sf JA}$	TSSOP-8	140	
		UDFN-8	350	
		SOIC-14	156]
		TSSOP-14	190	

OPERATING RANGES

THERMAL INFORMATION

Parameter	Symbol	Min	Max	Unit
Operating Supply Voltage	V _S	2.7	36	V
Differential Input Voltage	V_{ID}		V_S	V
Input Common Mode Range	V_{ICM}	V_{SS}	V _{DD} – 1.35	V
Ambient Temperature	T _A	-40	125	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ELECTRICAL CHARACTERISTICS AT $V_S = 2.7 \text{ V}$

 $T_A = 25^{\circ}\text{C}$; $R_L \ge 10 \text{ k}\Omega$; $V_{CM} = V_{OUT} = \text{mid-supply}$ unless otherwise noted. All limits are guaranteed by testing or statistical analysis. **Boldface** limits apply over the specified temperature range, $T_A = -40^{\circ}\text{C}$ to 125°C. (Notes 6, 7)

Parameter	Symbol	Cond	itions	Min	Тур	Max	Unit
INPUT CHARACTERISTICS							
Innut Offeet Velter -	V				1.3	±3	mV
Input Offset Voltage	V _{OS}					±4	mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	T _A = 25°C	to 125°C		2		μV/°C
Input Bias Current	l.=	No	te 7		5	200	pА
Input bias Current	I _{IB}	NO	ie i			1500	pА
Input Offset Current	los	No	te 7		2	75	pА
Input Onset Ourrent	iOS	140	ie i			175	pА
Channel Separation	XTLK	С	C		115		dB
Differential Input Resistance	R_{ID}				50		GΩ
Common Mode Input Resistance	R _{IN}				5		GΩ
Differential Input Capacitance	C _{ID}				1.5		pF
Common Mode Input Capacitance	C _{CM}				3.5		pF
Common Mode Rejection Ratio	CMRR	Vo 0 V to	V _{CM} = 0 V to V _{DD} - 1.35 V		110		dB
Common Wode Hejection Hatio	OWNT	VCM = 0 ∧ 10	V _{DD} = 1.00 V	69			GD.
OUTPUT CHARACTERISTICS					_		
Open Loop Voltage Gain	A_{VOL}			96	118		dB
Open Loop vollage dam	AVOL			86			ub
Output Current Capability	Io	Op amp sin	king current		70		mA
output outroin oupubling	.0	Op amp sou	rcing current		50		111/1
Output Voltage High	V _{OH}	Voltage output swi	ng from positive rail		0.006	0.15	V
Output voltage Flight	VOH	voltage output swi	ng irom positive rail			0.22	V
Output Voltage Low	V _{OL}	Voltage output swir	ng from negative rail		0.005	0.15	V
Output voltage Low	VOL	voltage output swii	ig nom negative ran			0.22	V
AC CHARACTERISTICS					_		
Unity Gain Bandwidth	UGBW	C _L =	25 pF		3		MHz
Slew Rate at Unity Gain	SR		20 pF		2.8		V/μs
Phase Margin	$\phi_{\boldsymbol{m}}$	C _L =	25 pF		50		0
Gain Margin	A_{m}	C _L =	25 pF		14		dB
Settling Time	t _S	V _O = 1 Vpp,	Settling time to 0.1%		0.6		116
Colling Time	٠,٥	Gain = 1, C _L = 20 pF Settling time to 0.01%			1.2		μs
NOISE CHARACTERISTICS							
Total Harmonic Distortion plus Noise	THD+N	V _{IN} = 0.5 Vpp, 1	= 1 kHz, Av = 1		0.05		%
Input Referred Voltage Noise	e _n	f = 1 kHz			30		nV/√Hz
mpar releited voilage Noise	₽n	f = 10 kHz			20		110/11/2
Input Referred Current Noise	i _n	f = 1 kHz			0.25	<u></u>	fA/√Hz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. Refer to ABSOLUTE MAXIMUM RATINGS and APPLICATION INFORMATION for Safe Operating Area.

^{7.} Performance guaranteed over the indicated operating temperature range by design and/or characterization.

ELECTRICAL CHARACTERISTICS AT $V_S = 2.7 \text{ V}$

 $T_A = 25^{\circ}\text{C}$; $R_L \ge 10 \text{ k}\Omega$; $V_{CM} = V_{OUT} = \text{mid}$ -supply unless otherwise noted. All limits are guaranteed by testing or statistical analysis. **Boldface** limits apply over the specified temperature range, $T_A = -40^{\circ}\text{C}$ to 125°C. (Notes 6, 7)

Parameter	Symbol	Conditions		Min	Тур	Max	Unit
SUPPLY CHARACTERISTICS							
	DODD	Nelsed		114	135		4D
Power Supply Rejection Ratio	PSRR	No Load		100			dB
De la Carta Carta Carta	,	December and an local			405	525	
Power Supply Quiescent Current	I _{DD}	Per channel, no load				625	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 6. Refer to ABSOLUTE MAXIMUM RATINGS and APPLICATION INFORMATION for Safe Operating Area.
- 7. Performance guaranteed over the indicated operating temperature range by design and/or characterization.

ELECTRICAL CHARACTERISTICS AT V_S = 5 V

 $T_A = 25^{\circ}\text{C}$; $R_L \ge 10 \text{ k}\Omega$; $V_{CM} = V_{OUT} = \text{mid-supply}$ unless otherwise noted. All limits are guaranteed by testing or statistical analysis. **Boldface** limits apply over the specified temperature range, $T_A = -40^{\circ}\text{C}$ to 125°C. (Notes 8, 9)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
INPUT CHARACTERISTICS						
Innut Offact Valtage	.,			1.3	±3	mV
Input Offset Voltage	V _{OS}				±4	mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	T _A = 25°C to 125 °C		2		μV/°C
Input Bias Current		Note 9		5	200	pА
input bias current	I _{IB}	Note 9			1500	pА
Input Offset Current	la a	Note 9		2	75	pА
Input Onset Current	los	Note 9			175	pА
Channel Separation	XTLK	DC		115		dB
Differential Input Resistance	R_{ID}			50		GΩ
Common Mode Input Resistance	R _{IN}			5		GΩ
Differential Input Capacitance	C _{ID}			1.5		pF
Common Mode Input Capacitance	C _{CM}			3.5		pF
Common Mada Dajastian Datia	OMDD	V 0V/toV 125V	105	125		٩D
Common Mode Rejection Ratio	CMRR	$V_{CM} = 0 \text{ V to } V_{DD} - 1.35 \text{ V}$	80			dB
OUTPUT CHARACTERISTICS						
Onen Leen Veltage Coin	^		96	120		dB
Open Loop Voltage Gain	A _{VOL}		86			αБ
Outrot Outrot Constille	,	Op amp sinking current		50		0
Output Current Capability	I _O	Op amp sourcing current		60		mA
Output Valtage High	V	Valtage output output from positive rail		0.013	0.20	V
Output Voltage High	V _{OH}	Voltage output swing from positive rail			0.25	7 °
Output Valtage Levi	\/	Voltage output outing from nogetime and		0.01	0.10	\ <u>\</u>
Output Voltage Low	V _{OL} Voltag	Voltage output swing from negative rail			0.15	·

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 8. Refer to ABSOLUTE MAXIMUM RATINGS and APPLICATION INFORMATION for Safe Operating Area.
- 9. Performance guaranteed over the indicated operating temperature range by design and/or characterization.

ELECTRICAL CHARACTERISTICS AT V_S = 5 V

 $T_A = 25^{\circ}\text{C}$; $R_L \ge 10 \text{ k}\Omega$; $V_{CM} = V_{OUT} = \text{mid-supply}$ unless otherwise noted. All limits are guaranteed by testing or statistical analysis. **Boldface** limits apply over the specified temperature range, $T_A = -40^{\circ}\text{C}$ to 125°C. (Notes 8, 9)

Parameter	Symbol	Cond	litions	Min	Тур	Max	Unit	
AC CHARACTERISTICS		•					•	
Unity Gain Bandwidth	UGBW	C _L =	25 pF		3.2		MHz	
Slew Rate at Unity Gain	SR	C _L =	20 pF		2.7		V/μs	
Phase Margin	ϕ_{m}	C _L =	25 pF		50		٥	
Gain Margin	A _m	C _L =	25 pF		14		dB	
Outline Tree		V _O = 3 Vpp,	Settling time to 0.1%		1.2			
Settling Time	t _S	Gain = 1, C _L = 20 pF Settl	Settling time to 0.01%		5.6		μs	
NOISE CHARACTERISTICS			·					
Total Harmonic Distortion plus Noise	THD+N	V _{IN} = 2.5 Vpp,	= 1 kHz, Av = 1		0.009		%	
January Deferment Voltages Nicios		f = 1	kHz		30		->///	
Input Referred Voltage Noise	e _n	f = 1	0 kHz		20		nV/√Hz	
Input Referred Current Noise	i _n	f = 1	kHz		0.25		fA/√ Hz	
SUPPLY CHARACTERISTICS								
D 0 1 D : " D "				114	135		I.D.	
Power Supply Rejection Ratio	PSRR	SRR No Load		100			dB	
D 0 10: 10 1	1					410	530	
Power Supply Quiescent Current	I _{DD}	Per channel, no load				630	μΑ	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 8. Refer to ABSOLUTE MAXIMUM RATINGS and APPLICATION INFORMATION for Safe Operating Area.
- 9. Performance guaranteed over the indicated operating temperature range by design and/or characterization.

ELECTRICAL CHARACTERISTICS AT $V_S = 10 \text{ V}$

 $T_A = 25^{\circ}C$; $R_L \ge 10 \text{ k}\Omega$; $V_{CM} = V_{OUT} = \text{mid}$ -supply unless otherwise noted. All limits are guaranteed by testing or statistical analysis. Boldface limits apply over the specified temperature range, $T_A = -40^{\circ}C$ to 125°C. (Notes 10, 11)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
INPUT CHARACTERISTICS			•		•	•
Input Offset Voltage	V			1.3	±3	mV
Input Offset Voltage	V _{OS}				±4	mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	T _A = 25°C to 125°C		2		μV/°C
Input Bias Current	I _{IB}	Note 11		5	200	pА
					1500	pА
Innut Offset Comment		Note 11		2	2 75	pА
Input Offset Current	los	Note 11		2	175	pА
Channel Separation	XTLK	DC		115		dB
Differential Input Resistance	R _{ID}			50		GΩ
Common Mode Input Resistance	R _{IN}			5		GΩ
Differential Input Capacitance	C _{ID}			1.5		pF
Common Mode Input Capacitance	C _{CM}			3.5		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 10. Refer to ABSOLUTE MAXIMUM RATINGS and APPLICATION INFORMATION for Safe Operating Area.
- 11. Performance guaranteed over the indicated operating temperature range by design and/or characterization.

ELECTRICAL CHARACTERISTICS AT V_S = 10 V $T_A = 25^{\circ}C$; $R_L \ge 10$ kΩ; $V_{CM} = V_{OUT} = \text{mid}$ –supply unless otherwise noted. All limits are guaranteed by testing or statistical analysis. Boldface limits apply over the specified temperature range, $T_A = -40^{\circ}C$ to 125°C. (Notes 10, 11)

Parameter	Symbol	Cond	itions	Min	Тур	Max	Unit
INPUT CHARACTERISTICS							•
	01400			110	130		
Common Mode Rejection Ratio	CMRR	$V_{CM} = 0 \text{ V to}$	V _{DD} – 1.35 V	87			dB
OUTPUT CHARACTERISTICS							•
Open Loop Voltage Gain	۸			98	120		dB
Open Loop vollage Gain	A _{VOL}			88			uБ
Output Current Capability	l _a	Op amp sin	king current		50		mA
Output Current Capability	I _O	Op amp sou	rcing current		65		IIIA
Output Voltage High	V	Voltago output awii	ng from positivo roil		0.023	0.08	V
Output voltage High	V _{OH}	voltage output swi	Voltage output swing from positive rail			0.10	V
Output Voltago Low	V	Voltago output swir	ng from pogativo rail		0.022	0.3	V
Output Voltage Low	V _{OL}	voltage output swii	ng from negative rail			0.35	, v
AC CHARACTERISTICS							
Unity Gain Bandwidth	UGBW	C _L = 25 pF			3.2		MHz
Slew Rate at Unity Gain	SR	C _L =	20 pF		2.2		V/μs
Phase Margin	ϕ_{m}	C _L =	25 pF		50		0
Gain Margin	A _m	C _L =	25 pF		14		dB
O.W The		$V_0 = 8.5 \text{ Vpp},$	Settling time to 0.1%		3.4		_
Settling Time	t _S	$V_O = 8.5 \text{ Vpp},$ Gain = 1, $C_L = 20 \text{ pF}$	Settling time to 0.01%		6.8		μS
NOISE CHARACTERISTICS							
Total Harmonic Distortion plus Noise	THD+N	V _{IN} = 7.5 Vpp, 1	= 1 kHz, Av = 1		0.004		%
January Defermed Velte as Noise	_	f = 1	kHz		30		->///
Input Referred Voltage Noise	e _n	f = 1	0 kHz		20		nV/√ Hz
Input Referred Current Noise	i _n	f = 1	kHz		0.25		fA/√ Hz
SUPPLY CHARACTERISTICS							
Dower Cumby Dejection Datio	PSRR	No Load		114	135		dB
Power Supply Rejection Ratio	ronn			100			l ub
Power Supply Quiescent Current	I	Per channel, no load			416	540	^
Tower Supply Quiescent Current	I _{DD}					640	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

10. Refer to ABSOLUTE MAXIMUM RATINGS and APPLICATION INFORMATION for Safe Operating Area.

11. Performance guaranteed over the indicated operating temperature range by design and/or characterization.

ELECTRICAL CHARACTERISTICS AT V_S = **36 V** $T_A = 25^{\circ}C$; $R_L \ge 10 \text{ k}\Omega$; $V_{CM} = V_{OUT} = \text{mid}$ –supply unless otherwise noted. All limits are guaranteed by testing or statistical analysis. Boldface limits apply over the specified temperature range, $T_A = -40^{\circ}C$ to 125°C. (Notes 12, 13)

Parameter	Symbol	Cond	itions	Min	Тур	Max	Unit
INPUT CHARACTERISTICS							
Innut Offeet Velters	V				1.3	±3	mV
Input Offset Voltage	Vos					±4	mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	T _A = 25°C	to 125°C		2		μV/°C
Input Bias Current	I	Note	n 10		5	200	pА
Input bias Current	I _{IB}	Note	e 13			1500	pА
Input Offset Current	loo	Note	e 13		2	75	pА
Input Onset Guirent	los	Note	9 13			175	pА
Channel Separation	XTLK	D	С		115		dB
Differential Input Resistance	R_{ID}				50		GΩ
Common Mode Input Resistance	R_{IN}				5		GΩ
Differential Input Capacitance	C _{ID}				1.5		pF
Common Mode Input Capacitance	C _{CM}				3.5		pF
Common Mode Rejection Ratio	CMRR	V _{CM} = 0 V to	V 135 V	120	145		dB
Common Mode Rejection Ratio	CIVILL	VCW = 0 A 10	V _{DD} - 1.33 V	95			uБ
OUTPUT CHARACTERISTICS							
Open Loop Voltage Gain	Δ			98	120		dB
Open Loop Vollage Gain	A_{VOL}			88			uБ
Output Current Capability	lo	Op amp sin	king current		50		mA
опригоптент оаравшту	lo	Op amp sou	rcing current		65		ША
Output Voltage High	V _{OH}	Voltage output swir	ng from positive rail		0.074	0.10	
Output voitage riigii	VOH	voltage output swii	ig irom positive rail			0.12	-
Output Voltage Low	V _{OL}	Voltage output swin	ng from negative rail		0.065	0.3	V
Output voltage Low	VOL	voltage output swii	ig ironi negative ran			0.35	V
AC CHARACTERISTICS							
Unity Gain Bandwidth	UGBW	$C_L = 1$	25 pF		3.2		MHz
Slew Rate at Unity Gain	SR	$C_L = 1$	20 pF		2.4		V/μs
Phase Margin	ϕ_{m}	$C_L = 1$	25 pF		50		0
Gain Margin	A _m	$C_L = 3$	25 pF		14		dB
Settling Time	+_	V _O = 10 Vpp,	Settling time to 0.1%		3.2		
Settling Time	t _S	Gain = 1, C _L = 20 pF Settling time to 0.01%			6.8		μS
NOISE CHARACTERISTICS							
Total Harmonic Distortion plus Noise	THD+N	V _{IN} = 28.5 Vpp,	f = 1 kHz, Av = 1		0.001		%
Input Referred Voltage Noise	-	f = 1	kHz		30		nV/√ Hz
input neterieu voltage Noise	e _n	f = 10) kHz		20		IIV/∀⊓Z
Input Referred Current Noise	i _n	f = 1	kHz		0.25		fA/√Hz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

12. Refer to ABSOLUTE MAXIMUM RATINGS and APPLICATION INFORMATION for Safe Operating Area.

^{13.} Performance guaranteed over the indicated operating temperature range by design and/or characterization.

ELECTRICAL CHARACTERISTICS AT V_S = **36 V** $T_A = 25^{\circ}C$; $R_L \ge 10 \text{ k}\Omega$; $V_{CM} = V_{OUT} = \text{mid}$ –supply unless otherwise noted. All limits are guaranteed by testing or statistical analysis. Boldface limits apply over the specified temperature range, $T_A = -40^{\circ}C$ to 125°C. (Notes 12, 13)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
SUPPLY CHARACTERISTICS						
0 10: " 0"	DODD		114	135		ID.
Power Supply Rejection Ratio	PSRR	No Load	100			dB
Dawer Cumply Ordersont Current	scent Current I _{DD} Per channel, no load		465	600	^	
Power Supply Quiescent Current		Per channel, no load			700	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

12. Refer to ABSOLUTE MAXIMUM RATINGS and APPLICATION INFORMATION for Safe Operating Area.

^{13.} Performance guaranteed over the indicated operating temperature range by design and/or characterization.

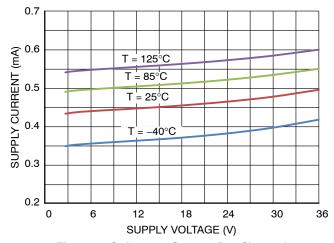


Figure 3. Quiescent Current Per Channel vs. **Supply Voltage**

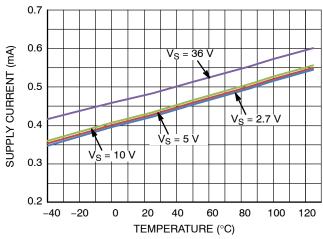


Figure 4. Quiescent Current vs. Temperature

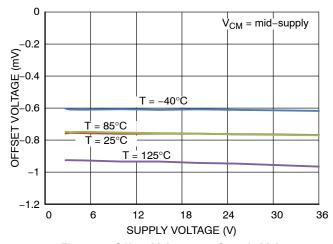


Figure 5. Offset Voltage vs. Supply Voltage

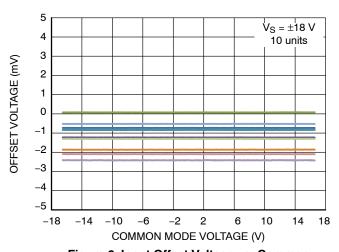


Figure 6. Input Offset Voltage vs. Common **Mode Voltage**

180

135

90

45

-90

-135

-180

10M

1M

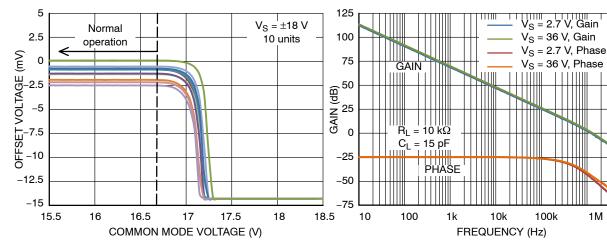


Figure 7. Input Offset Voltage vs. Common **Mode Voltage**

Figure 8. Gain and Phase vs. Frequency

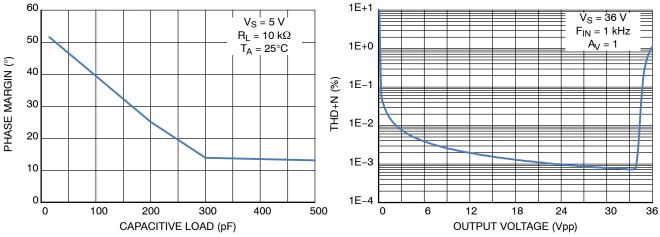


Figure 9. Phase Margin vs. Capacitive Load

Figure 10. THD+N vs. Output Voltage

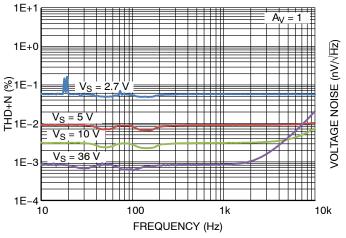


Figure 11. THD+N vs. Frequency

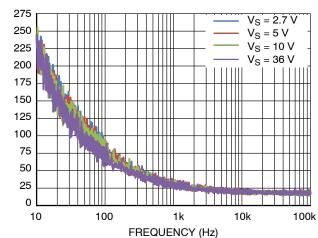


Figure 12. Input Voltage Noise vs. Frequency

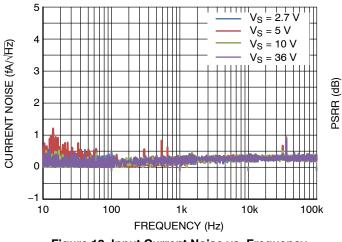


Figure 13. Input Current Noise vs. Frequency

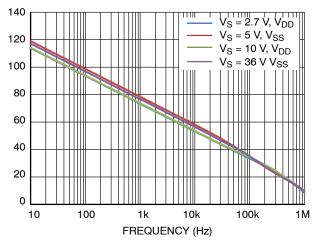
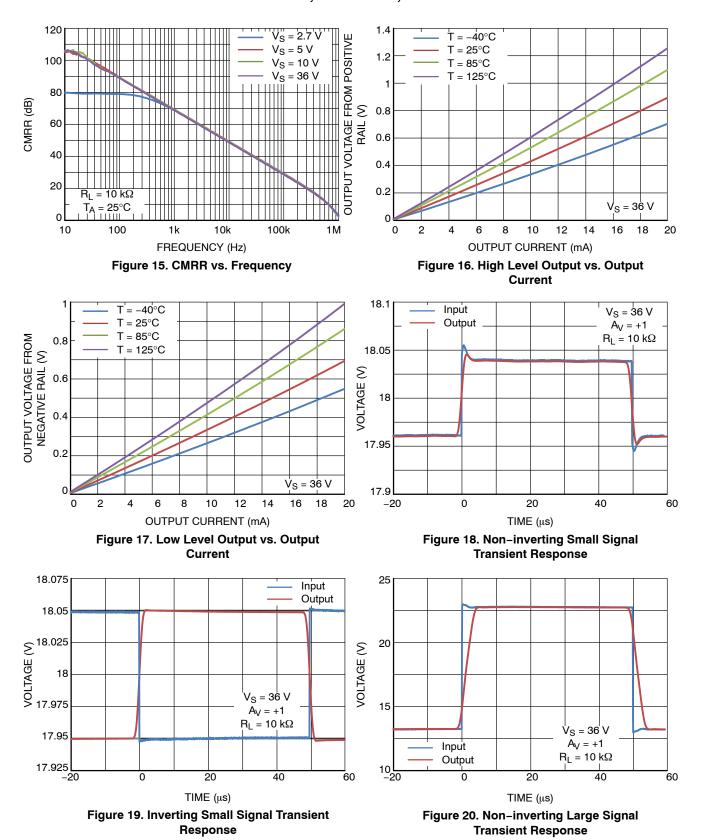


Figure 14. PSRR vs. Frequency



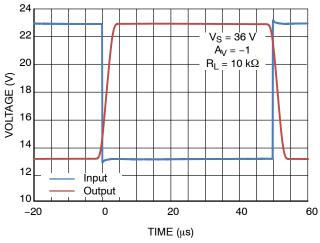


Figure 21. Inverting Large Signal Transient Response

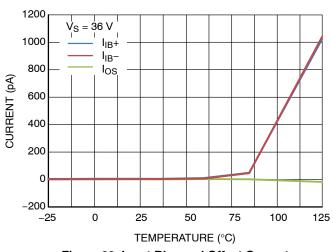


Figure 22. Input Bias and Offset Current vs.
Temperature

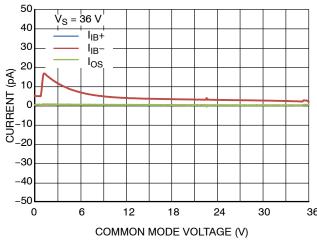


Figure 23. Input Bias Current vs. Common Mode Voltage

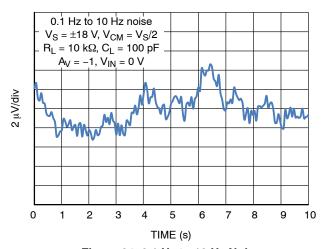


Figure 24. 0.1 Hz to 10 Hz Noise

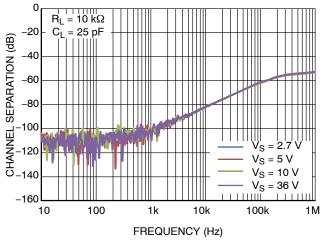


Figure 25. Channel Separation vs. Frequency

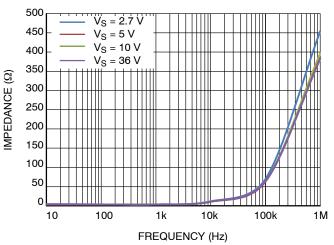


Figure 26. Open Loop Output Impedance

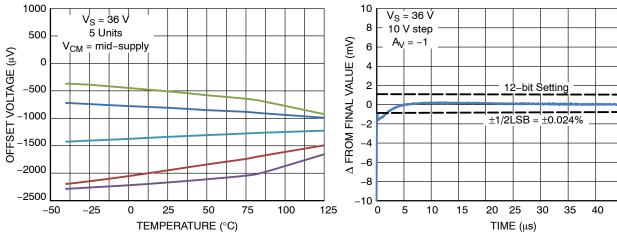


Figure 27. Offset Voltage vs. Temperature

Figure 28. Large Signal Settling Time

45

50

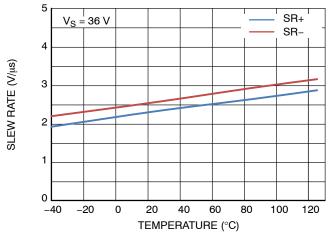
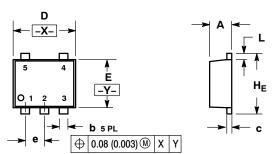


Figure 29. Slew Rate vs. Temperature

PACKAGE DIMENSIONS

SOT-553, 5 LEAD

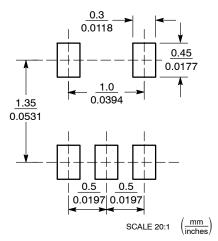
CASE 463B ISSUE C



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
 THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM
 THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.50	0.55	0.60	0.020	0.022	0.024
b	0.17	0.22	0.27	0.007	0.009	0.011
С	0.08	0.13	0.18	0.003	0.005	0.007
D	1.55	1.60	1.65	0.061	0.063	0.065
E	1.15	1.20	1.25	0.045	0.047	0.049
е	0.50 BSC			0.020 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.55	1.60	1.65	0.061	0.063	0.065

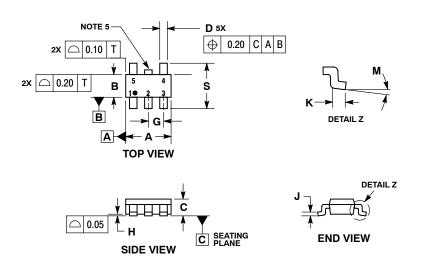
RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSOP-5 CASE 483-02 ISSUE K

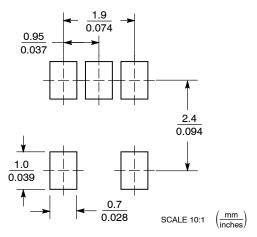


NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME
- Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A.
 OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION
- TRIMMED LEAD IS ALLOWED IN THIS LOCATION.
 TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2

	MILLIMETERS				
DIM	MIN	MAX			
Α	3.00	3.00 BSC			
В	1.50	1.50 BSC			
С	0.90	1.10			
D	0.25	0.50			
G	0.95 BSC				
Н	0.01	0.10			
J	0.10	0.26			
K	0.20	0.60			
M	0° 10°				
S	2.50 3.00				

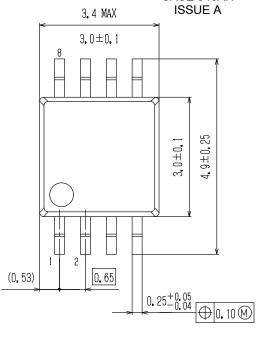
SOLDERING FOOTPRINT*

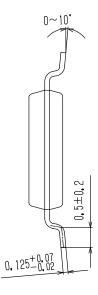


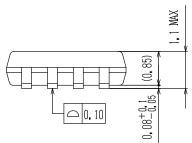
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

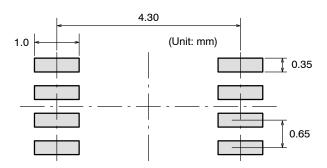
Micro8 / MSOP8 (150 mil) CASE 846AH







SOLDERING FOOTPRINT*

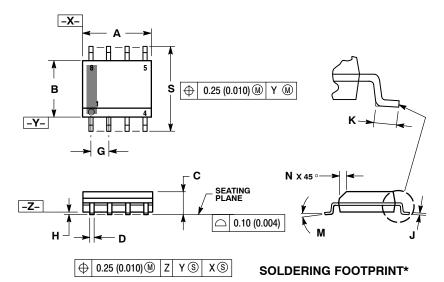


NOTE: The measurements are not to guarantee but for reference only.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and

PACKAGE DIMENSIONS

SOIC-8 NB CASE 751-07 **ISSUE AK**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

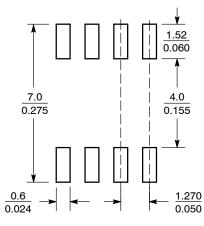
 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.

 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) DED SIDE

- . MAXIMUM MOLD PROTRUSION 0.15 (0.006)
 PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.
 751-01 THRU 751-06 ARE OBSOLETE. NEW
 STANDAD IS 751-07
- STANDARD IS 751-07.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
М	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

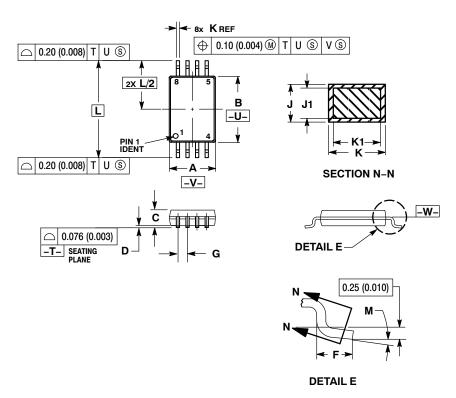


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SCALE 6:1

PACKAGE DIMENSIONS

TSSOP-8 CASE 948S-01 **ISSUE C**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010)
- PER SIDE.

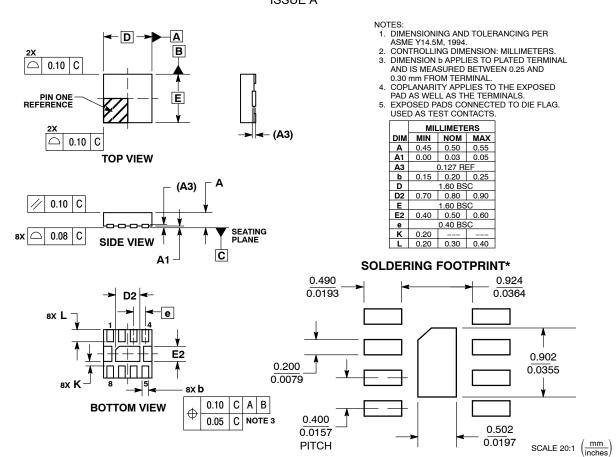
 5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE W –.

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.114	0.122
В	4.30	4.50	0.169	0.177
C		1.10		0.043
D	0.05	0.15	0.002	0.006
F	0.50	0.70	0.020	0.028
G	0.65 BSC		0.026 BSC	
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0°	8°	0°	8°

PACKAGE DIMENSIONS

UDFN8, 1.6x1.6, 0.4P CASE 517AC-01 **ISSUE A**

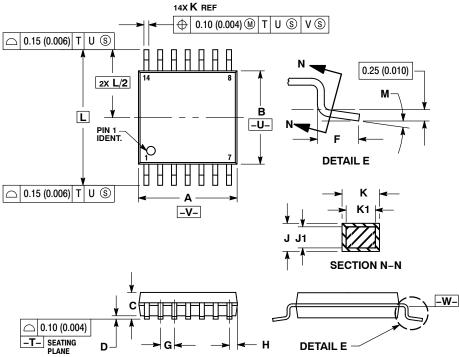


PITCH

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP-14 CASE 948G-01 **ISSUE B**

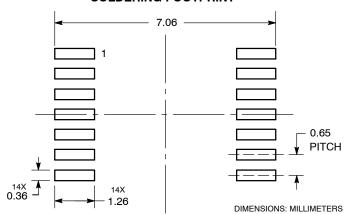


NOTES:

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD
 FLASH, PROTRUSIONS OR GATE BURRS.
 MOLD FLASH OR GATE BURRS SHALL NOT
 EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
 NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL
 IN EXCESS OF THE K DIMENSION AT
- IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65 BSC		0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
Κ	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
Г	6.40 BSC		0.252 BSC		
М	0 °	8 °	0 °	8 °	

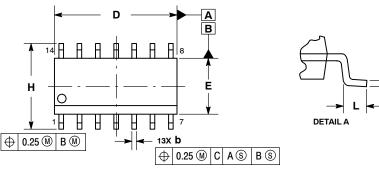
SOLDERING FOOTPRINT*

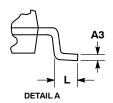


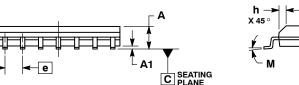
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOIC-14 NB CASE 751A-03 ISSUE K







NOTES:

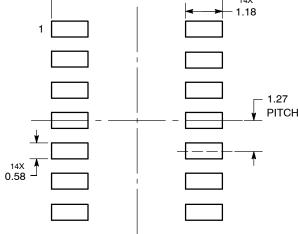
DETAIL A

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION & DOES NOT INCLUDE DAMBAR PROTRUSION, ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
- 4. DIMENSIONS D AND E DO NOT INCLUDE
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
е	1.27 BSC		0.050 BSC	
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7°	0 °	7°

6.50 14X 1.18

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

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